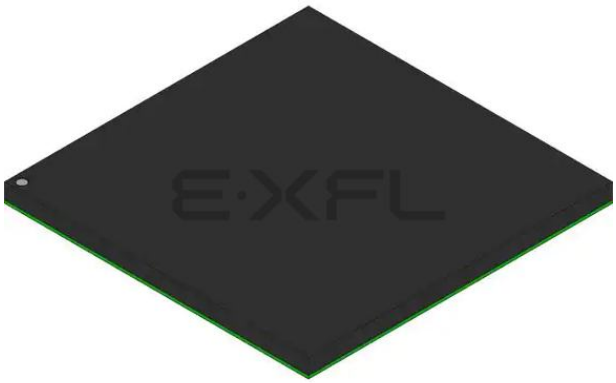

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Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	533MHz
Co-Processors/DSP	-
RAM Controllers	DDR
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	672-LBGA
Supplier Device Package	672-LBGA (35x35)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8347vvajd

6 DDR SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the MPC8347E.

NOTE

The information in this document is accurate for revision 1.1 silicon and earlier. For information on revision 3.0 silicon and earlier versions see the *MPC8347EA PowerQUICC™ II Pro Integrated Host Processor Hardware Specifications.* See Section 23.1, "Part Numbers Fully Addressed by This Document," for silicon revision level determination.

6.1 DDR SDRAM DC Electrical Characteristics

Table 11 provides the recommended operating conditions for the DDR SDRAM component(s) of the MPC8347E.

Table 11. DDR SDRAM DC Electrical Characteristics

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.18$	$GV_{DD} + 0.3$	V	
Input low voltage	V_{IL}	–0.3	$MV_{REF} - 0.18$	V	
Output leakage current	I_{OZ}	–10	10	µA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–15.2	—	mA	
Output low current (V_{OUT} = 0.35 V)	I_{OL}	15.2	—	mA	
MV_{REF} input leakage current	I_{VREF}	—	5	µA	

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, $0 V \le V_{OUT} \le GV_{DD}$.

Table 12 provides the DDR capacitance.

Table 12. DDR SDRAM Capacitance

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

6.2 DDR SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM interface.

6.2.1 DDR SDRAM Input AC Timing Specifications

Table 13 provides the input AC timing specifications for the DDR SDRAM interface.

Table 13. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of 2.5 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.31	V	
AC input high voltage	V_{IH}	MV_{REF} + 0.31	GV_{DD} + 0.3	V	
MDQS—MDQ/MECC input skew per byte 333 MHz 266 MHz	t_{DISKEW}	—	 750 1125	ps	1

Note:

1. Maximum possible skew between a data strobe (MDQS[n]) and any corresponding bit of data (MDQ[8n + {0...7}] if 0 <= n <= 7) or ECC (MECC[{0...7}] if n = 8).

Figure 4 illustrates the DDR input timing diagram showing the t_{DISKEW} timing parameter.

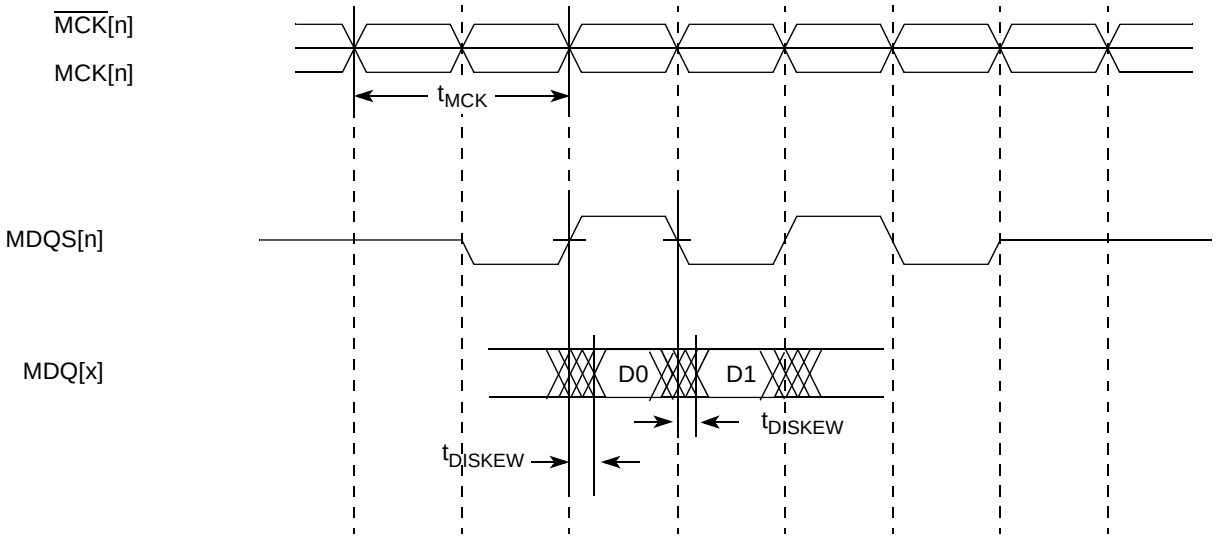

Figure 4. DDR Input Timing Diagram

6.2.2 DDR SDRAM Output AC Timing Specifications

Table 14 and Table 15 provide the output AC timing specifications and measurement conditions for the DDR SDRAM interface.

8 Ethernet: Three-Speed Ethernet, MII Management

This section provides the AC and DC electrical characteristics for three-speeds (10/100/1000 Mbps) and MII management.

8.1 Three-Speed Ethernet Controller (TSEC)— GMII/MII/TBI/RGMII/RTBI Electrical Characteristics

The electrical characteristics specified here apply to the gigabit media independent interface (GMII), the media independent interface (MII), ten-bit interface (TBI), reduced gigabit media independent interface (RGMII), and reduced ten-bit interface (RTBI) signals except management data input/output (MDIO) and management data clock (MDC). The MII, GMII, and TBI interfaces are defined for 3.3 V, and the RGMII and RTBI interfaces are defined for 2.5 V. The RGMII and RTBI interfaces follow the Hewlett-Packard *Reduced Pin-Count Interface for Gigabit Ethernet Physical Layer Device Specification*, Version 1.2a (9/22/2000). The electrical characteristics for MDIO and MDC are specified in Section 8.3, "Ethernet Management Interface Electrical Characteristics."

8.1.1 TSEC DC Electrical Characteristics

GMII, MII, TBI, RGMII, and RTBI drivers and receivers comply with the DC parametric attributes specified in Table 19 and Table 20. The RGMII and RTBI signals in Table 20 are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Table 19. GMII/TBI and MII DC Electrical Characteristics

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage 3.3 V	LV_{DD}[2]	—		2.97	3.63	V
Output high voltage	V_{OH}	I_{OH} = –4.0 mA	LV_{DD} = Min	2.40	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 4.0 mA	LV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—	—	2.0	LV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	—	–0.3	0.90	V
Input high current	I_{IH}	V_{IN}[1] = LV_{DD}		—	40	µA
Input low current	I_{IL}	V_{IN}[1] = GND		–600	—	µA

Notes:
1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.
2. GMII/MII pins not needed for RGMII or RTBI operation are powered by the OV_{DD} supply.

Table 20. RGMII/RTBI (When Operating at 2.5 V) DC Electrical Characteristics

Parameters	Symbol	Conditions		Min	Max	Unit
Supply voltage 2.5 V	LV_{DD}	—		2.37	2.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	LV_{DD} = Min	2.00	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	LV_{DD} = Min	GND – 0.3	0.40	V
Input high voltage	V_{IH}	—	LV_{DD} = Min	1.7	LV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	LV_{DD} = Min	–0.3	0.70	V
Input high current	I_{IH}	V_{IN}[1] = LV_{DD}		—	10	µA
Input low current	I_{IL}	V_{IN}[1] = GND		–15	—	µA

Note:
1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

8.2 GMII, MII, TBI, RGMII, and RTBI AC Timing Specifications

The AC timing specifications for GMII, MII, TBI, RGMII, and RTBI are presented in this section.

8.2.1 GMII Timing Specifications

This section describes the GMII transmit and receive AC timing specifications.

8.2.1.1 GMII Transmit AC Timing Specifications

Table 21 provides the GMII transmit AC timing specifications.

Table 21. GMII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
GTX_CLK clock period	t_{GTX}	—	8.0	—	ns
GTX_CLK duty cycle	t_{GTXH}/t_{GTX}	43.75	—	56.25	%
GTX_CLK to GMII data TXD[7:0], TX_ER, TX_EN delay	t_{GTKHDX}	0.5	—	5.0	ns
GTX_CLK clock rise time, V_{IL}(min) to V_{IH}(max)	t_{GTXR}	—	—	1.0	ns
GTX_CLK clock fall time, V_{IH}(max) to V_{IL}(min)	t_{GTXF}	—	—	1.0	ns
GTX_CLK125 clock period	t_{G125}[2]	—	8.0	—	ns
GTX_CLK125 reference clock duty cycle measured at $LV_{DD}/2$	t_{G125H}/t_{G125}	45	—	55	%

Notes:
1. The symbols for timing specifications follow the pattern $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GTKHDV} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) reaching the valid state (V) to state or setup time. Also, t_{GTKHDX} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) going invalid (X) or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{GTX} represents the GMII(G) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This symbol represents the external GTX_CLK125 signal and does not follow the original symbol naming convention.

Figure 8 shows the GMII transmit AC timing diagram.

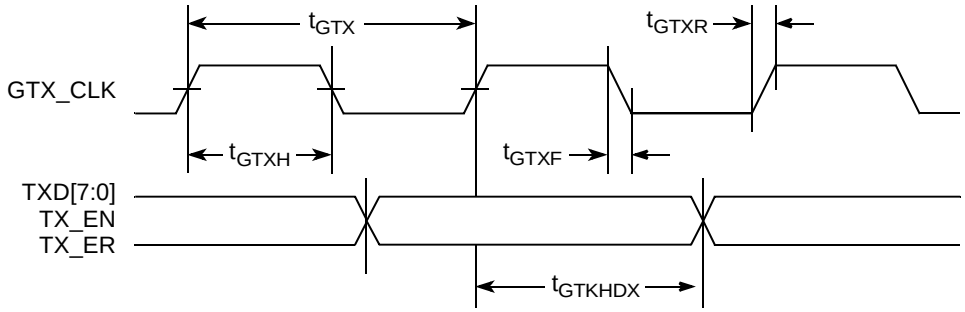

Figure 8. GMII Transmit AC Timing Diagram

8.2.1.2 GMII Receive AC Timing Specifications

Table 22 provides the GMII receive AC timing specifications.

Table 22. GMII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
RX_CLK clock period	t_{GRX}	—	8.0	—	ns
RX_CLK duty cycle	t_{GRXH}/t_{GRX}	40	—	60	%
RXD[7:0], RX_DV, RX_ER setup time to RX_CLK	t_{GRDVKH}	2.0	—	—	ns
RXD[7:0], RX_DV, RX_ER hold time to RX_CLK	t_{GRDXKH}	0.5	—	—	ns
RX_CLK clock rise, V_{IL}(min) to V_{IH}(max)	t_{GRXR}	—	—	1.0	ns
RX_CLK clock fall time, V_{IH}(max) to V_{IL}(min)	t_{GRXF}	—	—	1.0	ns

Note:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 12 shows the MII receive AC timing diagram.

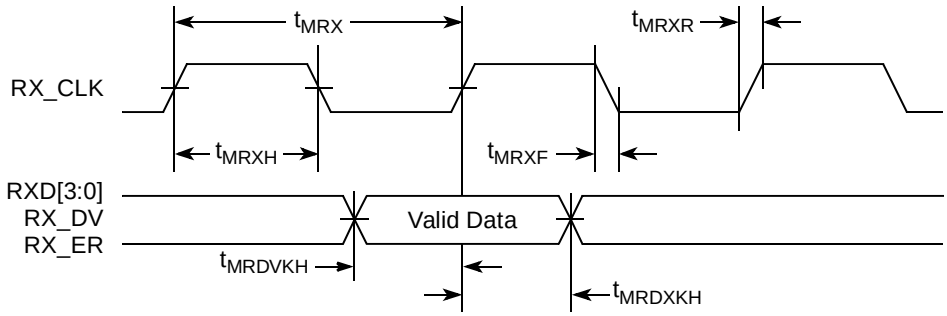

Figure 12. MII Receive AC Timing Diagram

8.2.3 TBI AC Timing Specifications

This section describes the TBI transmit and receive AC timing specifications.

8.2.3.1 TBI Transmit AC Timing Specifications

Table 25 provides the TBI transmit AC timing specifications.

Table 25. TBI Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
GTX_CLK clock period	t_{TTX}	—	8.0	—	ns
GTX_CLK duty cycle	t_{TTXH}/t_{TTX}	40	—	60	%
GTX_CLK to TBI data TXD[7:0], TX_ER, TX_EN delay	t_{TTKHDX}	1.0	—	5.0	ns
GTX_CLK clock rise, V_{IL}(min) to V_{IH}(max)	t_{TTXR}	—	—	1.0	ns
GTX_CLK clock fall time, V_{IH}(max) to V_{IL}(min)	t_{TTXF}	—	—	1.0	ns
GTX_CLK125 reference clock period	t_{G125}[2]	—	8.0	—	ns
GTX_CLK125 reference clock duty cycle	t_{G125H}/t_{G125}	45	—	55	ns

Notes:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{TTKHDV} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the valid state (V) or setup time. Also, t_{TTKHDX} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the invalid state (X) or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{TTX} represents the TBI (T) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This symbol represents the external GTX_CLK125 and does not follow the original symbol naming convention

Figure 13 shows the TBI transmit AC timing diagram.

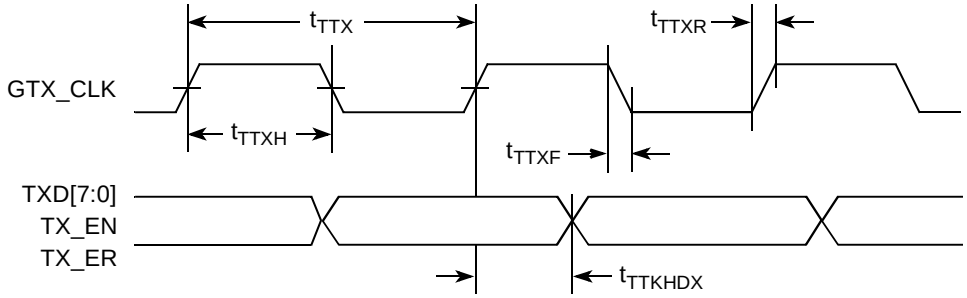

Figure 13. TBI Transmit AC Timing Diagram

8.2.3.2 TBI Receive AC Timing Specifications

Table 26 provides the TBI receive AC timing specifications.

Table 26. TBI Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
PMA_RX_CLK clock period	t_{TRX}		16.0		ns
PMA_RX_CLK skew	t_{SKTRX}	7.5	—	8.5	ns
RX_CLK duty cycle	t_{TRXH}/t_{TRX}	40	—	60	%
RXD[7:0], RX_DV, RX_ER (RCG[9:0]) setup time to rising PMA_RX_CLK	t_{TRDVKH}[2]	2.5	—	—	ns
RXD[7:0], RX_DV, RX_ER (RCG[9:0]) hold time to rising PMA_RX_CLK	t_{TRDXKH}[2]	1.5	—	—	ns
RX_CLK clock rise time V_{IL}(min) to V_{IH}(max)	t_{TRXR}	0.7	—	2.4	ns
RX_CLK clock fall time V_{IH}(max) to V_{IL}(min)	t_{TRXF}	0.7	—	2.4	ns

Notes:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{TRDVKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{TRX} clock reference (K) going to the high (H) state or setup time. Also, t_{TRDXKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) went invalid (X) relative to the t_{TRX} clock reference (K) going to the high (H) state. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{TRX} represents the TBI (T) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall). For symbols representing skews, the subscript SK followed by the clock that is being skewed (TRX).
2. Setup and hold time of even numbered RCG are measured from the riding edge of PMA_RX_CLK1. Setup and hold times of odd-numbered RCG are measured from the riding edge of PMA_RX_CLK0.

Figure 15 shows the RBMII and RTBI AC timing and multiplexing diagrams.

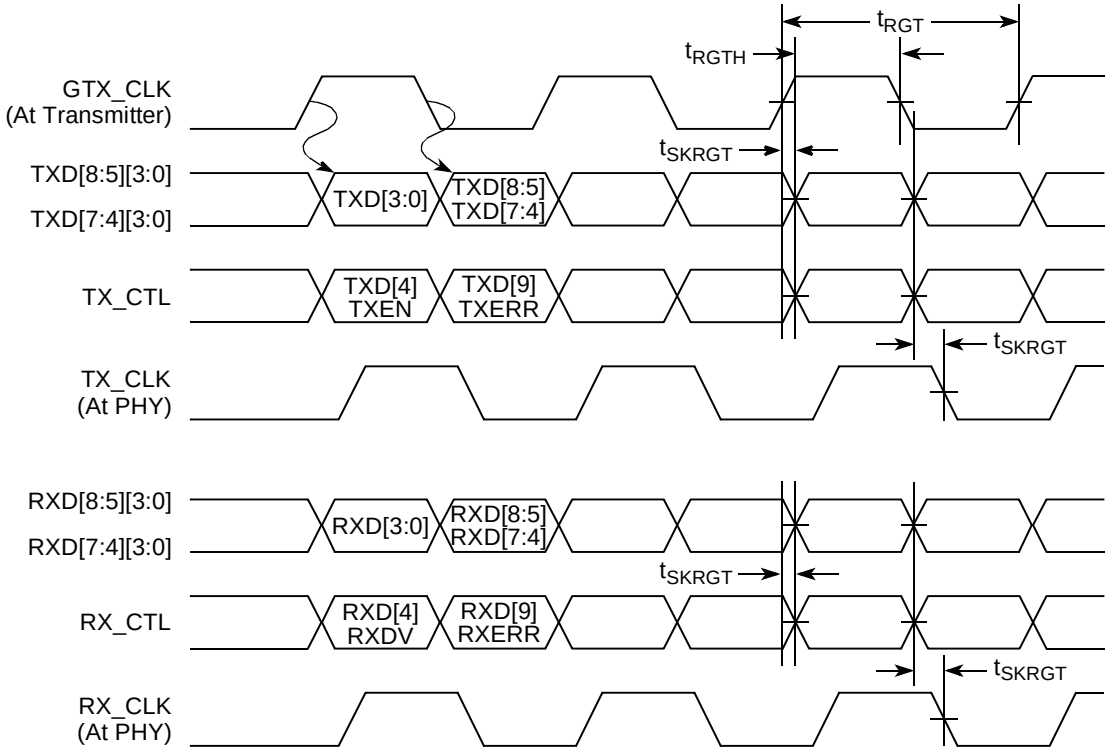

Figure 15. RGMII and RTBI AC Timing and Multiplexing Diagrams

Figure 20 through Figure 25 show the local bus signals.

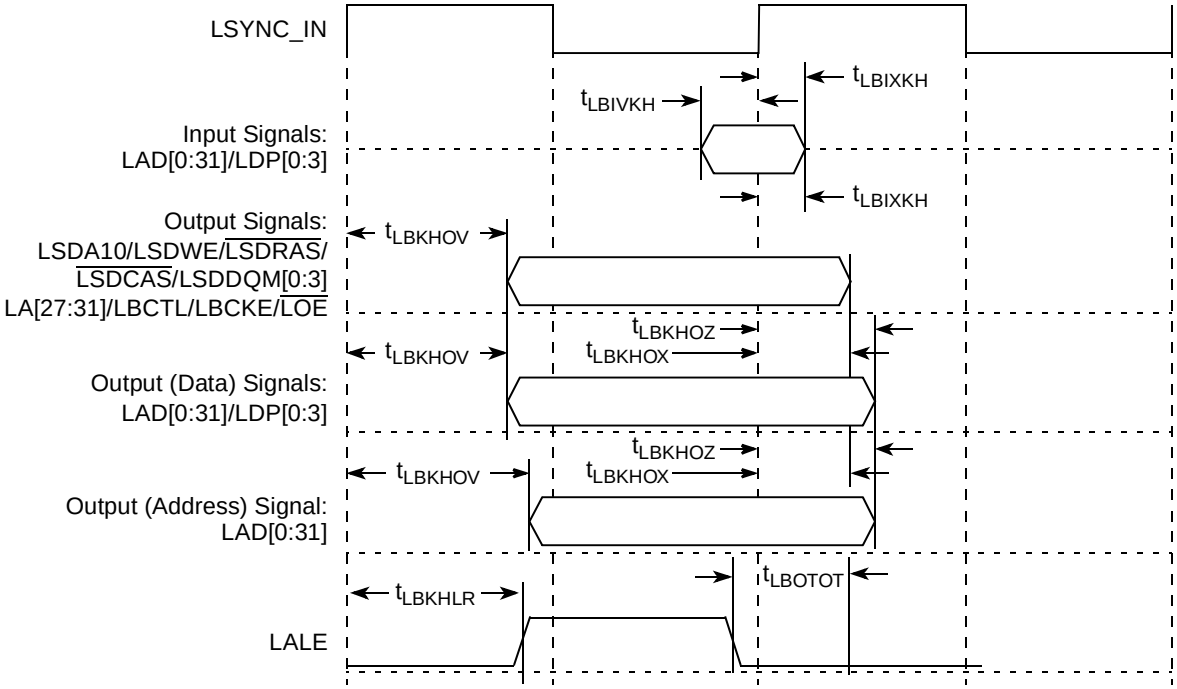

Figure 20. Local Bus Signals, Nonspecial Signals Only (DLL Enabled)

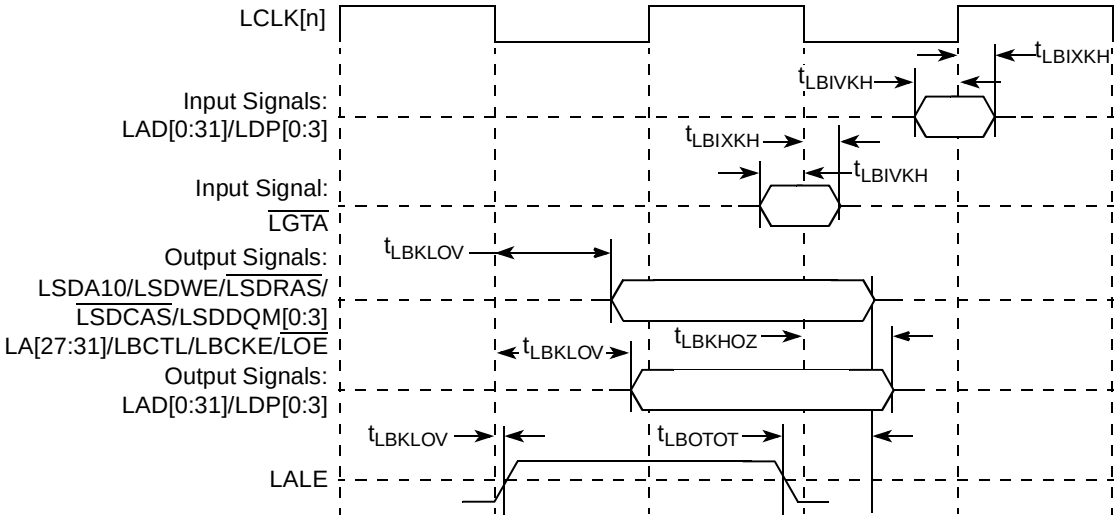

Figure 21. Local Bus Signals, Nonspecial Signals Only (DLL Bypass Mode)

15 GPIO

This section describes the DC and AC electrical specifications for the GPIO.

15.1 GPIO DC Electrical Characteristics

Table 45 provides the DC electrical characteristics for the MPC8347E GPIO.

Table 45. GPIO DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}		2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}		–0.3	0.8	V
Input current	I_{IN}			±5	μA
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

15.2 GPIO AC Timing Specifications

Table 46 provides the GPIO input and output AC timing specifications.

Table 46. GPIO Input AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Unit
GPIO inputs—minimum pulse width	t_{PIWID}	20	ns

Notes:

1. Input specifications are measured from the 50 percent level of the signal to the 50 percent level of the rising edge of CLKIN. Timings are measured at the pin.
2. GPIO inputs and outputs are asynchronous to any visible clock. GPIO outputs should be synchronized before use by external synchronous logic. GPIO inputs must be valid for at least t_{PIWID} ns to ensure proper operation.

18.5 Pinout Listings

Table 51 provides the pinout listing for the MPC8347E, 672 TBGA package.

Table 51. MPC8347E (TBGA) Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI				
PCI_INTA/IRQ_OUT	B34	O	OV_{DD}	2
PCI_RESET_OUT	C33	O	OV_{DD}	
PCI_AD[31:0]	G30, G32, G34, H31, H32, H33, H34, J29, J32, J33, L30, K31, K33, K34, L33, L34, P34, R29, R30, R33, R34, T31, T32, T33, U31, U34, V31, V32, V33, V34, W33, W34	I/O	OV_{DD}	
PCI_C/BE[3:0]	J30, M31, P33, T34	I/O	OV_{DD}	
PCI_PAR	P32	I/O	OV_{DD}	
PCI_FRAME	M32	I/O	OV_{DD}	5
PCI_TRDY	N29	I/O	OV_{DD}	5
PCI_IRDY	M34	I/O	OV_{DD}	5
PCI_STOP	N31	I/O	OV_{DD}	5
PCI_DEVSEL	N30	I/O	OV_{DD}	5
PCI_IDSEL	J31	I	OV_{DD}	
PCI_SERR	N34	I/O	OV_{DD}	5
PCI_PERR	N33	I/O	OV_{DD}	5
PCI_REQ[0]	D32	I/O	OV_{DD}	
PCI_REQ[1]/CPCI1_HS_ES	D34	I	OV_{DD}	
PCI_REQ[2:4]	E34, F32, G29	I	OV_{DD}	
PCI_GNT0	C34	I/O	OV_{DD}	
PCI_GNT1/CPCI1_HS_LED	D33	O	OV_{DD}	
PCI_GNT2/CPCI1_HS_ENUM	E33	O	OV_{DD}	
PCI_GNT[3:4]	F31, F33	O	OV_{DD}	
M66EN	A19	I	OV_{DD}	
DDR SDRAM Memory Interface				
MDQ[0:63]	D5, A3, C3, D3, C4, B3, C2, D4, D2, E5, G2, H6, E4, F3, G4, G3, H1, J2, L6, M6, H2, K6, L2, M4, N2, P4, R2, T4, P6, P3, R1, T2, AB5, AA3, AD6, AE4, AB4, AC2, AD3, AE6, AE3, AG4, AK5, AK4, AE2, AG6, AK3, AK2, AL2, AL1, AM5, AP5, AM2, AN1, AP4, AN5, AJ7, AN7, AM8, AJ9, AP6, AL7, AL9, AN8	I/O	GV_{DD}	

Table 51. MPC8347E (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MECC[0:4]/MSRCID[0:4]	W4, W3, Y3, AA6, T1	I/O	GV_{DD}	
MECC[5]/MDVAL	U1	I/O	GV_{DD}	
MECC[6:7]	Y1, Y6	I/O	GV_{DD}	
MDM[0:8]	B1, F1, K1, R4, AD4, AJ1, AP3, AP7, Y4	O	GV_{DD}	
MDQS[0:8]	B2, F5, J1, P2, AC1, AJ2, AN4, AL8, W2	I/O	GV_{DD}	
MBA[0:1]	AD1, AA5	O	GV_{DD}	
MA[0:14]	W1, U4, T3, R3, P1, M1, N1, L3, L1, K2, Y2, K3, J3, AP2, AN6	O	GV_{DD}	
$\overline{\text{MWE}}$	AF1	O	GV_{DD}	
$\overline{\text{MRAS}}$	AF4	O	GV_{DD}	
$\overline{\text{MCAS}}$	AG3	O	GV_{DD}	
$\overline{\text{MCS}}$[0:3]	AG2, AG1, AK1, AL4	O	GV_{DD}	
MCKE[0:1]	H3, G1	O	GV_{DD}	3
MCK[0:5]	U2, F4, AM3, V3, F2, AN3	O	GV_{DD}	
$\overline{\text{MCK}}$[0:5]	U3, E3, AN2, V4, E1, AM4	O	GV_{DD}	
Pins Reserved for Future DDR2 (They should be left unconnected for MPC8347)				
MODT[0:3]	AH3, AJ5, AH1, AJ4	—	—	
MBA[2]	H4	—	—	
SPARE1	AA1	—	—	8
SPARE2	AB1	—	—	6
Local Bus Controller Interface				
LAD[0:31]	AM13, AP13, AL14, AM14, AN14, AP14, AK15, AJ15, AM15, AN15, AP15, AM16, AL16, AN16, AP16, AL17, AM17, AP17, AK17, AP18, AL18, AM18, AN18, AP19, AN19, AM19, AP20, AK19, AN20, AL20, AP21, AN21	I/O	OV_{DD}	
LDP[0]/$\overline{\text{CKSTOP\_OUT}}$	AM21	I/O	OV_{DD}	
LDP[1]/$\overline{\text{CKSTOP\_IN}}$	AP22	I/O	OV_{DD}	
LDP[2]	AN22	I/O	OV_{DD}	
LDP[3]	AM22	I/O	OV_{DD}	
LA[27:31]	AK21, AP23, AN23, AP24, AK22	O	OV_{DD}	
$\overline{\text{LCS}}$[0:3]	AN24, AL23, AP25, AN25	O	OV_{DD}	
$\overline{\text{LWE}}$[0:3]/LSDDQM[0:3]/$\overline{\text{LBS}}$[0:3]	AK23, AP26, AL24, AM25	O	OV_{DD}	

Table 51. MPC8347E (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
DUART				
UART_SOUT[1:2]/MSRCID[0:1]/LSRCID[0:1]	AK27, AN29	O	OV_{DD}	
UART_SIN[1:2]/MSRCID[2:3]/LSRCID[2:3]	AL28, AM29	I/O	OV_{DD}	
$\overline{\text{UART\_CTS}}$[1]/MSRCID4/LSRCID4	AP30	I/O	OV_{DD}	
$\overline{\text{UART\_CTS}}$[2]/MDVAL/ LDVAL	AN30	I/O	OV_{DD}	
$\overline{\text{UART\_RTS}}$[1:2]	AP31, AM30	O	OV_{DD}	
I^2C interface				
IIC1_SDA	AK29	I/O	OV_{DD}	2
IIC1_SCL	AP32	I/O	OV_{DD}	2
IIC2_SDA	AN31	I/O	OV_{DD}	2
IIC2_SCL	AM31	I/O	OV_{DD}	2
SPI				
SPIMOSI	AN32	I/O	OV_{DD}	
SPIMISO	AP33	I/O	OV_{DD}	
SPICLK	AK30	I/O	OV_{DD}	
SPISEL	AL31	I	OV_{DD}	
Clocks				
PCI_CLK_OUT[0:4]	AN9, AP9, AM10, AN10, AJ11	O	OV_{DD}	
PCI_SYNC_IN/PCI_CLOCK	AK12	I	OV_{DD}	
PCI_SYNC_OUT	AP11	O	OV_{DD}	3
RTC/PIT_CLOCK	AM32	I	OV_{DD}	
CLKIN	AM9	I	OV_{DD}	
JTAG				
TCK	E20	I	OV_{DD}	
TDI	F20	I	OV_{DD}	4
TDO	B20	O	OV_{DD}	3
TMS	A20	I	OV_{DD}	4
$\overline{\text{TRST}}$	B19	I	OV_{DD}	4
Test				
TEST	D22	I	OV_{DD}	6
TEST_SEL	AL13	I	OV_{DD}	7
PMC				
$\overline{\text{QUIESCE}}$	A18	O	OV_{DD}	

Table 51. MPC8347E (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
System Control				
$\overline{\text{PORESET}}$	C18	I	OV_{DD}	
$\overline{\text{HRESET}}$	B18	I/O	OV_{DD}	1
$\overline{\text{SRESET}}$	D18	I/O	OV_{DD}	2
Thermal Management				
THERM0	K32	I	—	9
Power and Ground Signals				
$AV_{DD}1$	L31	Power for e300 PLL (1.2 V)	$AV_{DD}1$	
$AV_{DD}2$	AP12	Power for system PLL (1.2 V)	$AV_{DD}2$	
$AV_{DD}3$	AE1	Power for DDR DLL (1.2 V)	$AV_{DD}3$	
$AV_{DD}4$	AJ13	Power for LBIU DLL (1.2 V)	$AV_{DD}4$	
GND	A1, A34, C1, C7, C10, C11, C15, C23, C25, C28, D1, D8, D20, D30, E7, E13, E15, E17, E18, E21, E23, E25, E32, F6, F19, F27, F30, F34, G31, H5, J4, J34, K30, L5, M2, M5, M30, M33, N3, N5, P30, R5, R32, T5, T30, U6, U29, U33, V2, V5, V30, W6, W30, Y30, AA2, AA30, AB2, AB6, AB30, AC3, AC6, AD31, AE5, AF2, AF5, AF31, AG30, AG31, AH4, AJ3, AJ19, AJ22, AK7, AK13, AK14, AK16, AK18, AK20, AK25, AK28, AL3, AL5, AL10, AL12, AL22, AL27, AM1, AM6, AM7, AN12, AN17, AN34, AP1, AP8, AP34	—	—	
GV_{DD}	A2, E2, G5, G6, J5, K4, K5, L4, N4, P5, R6, T6, U5, V1, W5, Y5, AA4, AB3, AC4, AD5, AF3, AG5, AH2, AH5, AH6, AJ6, AK6, AK8, AK9, AL6	Power for DDR DRAM I/O voltage (2.5 V)	GV_{DD}	
$LV_{DD}1$	C9, D11	Power for three-speed Ethernet #1 and for Ethernet management interface I/O (2.5 V, 3.3 V)	$LV_{DD}1$	

As shown in Figure 41, the primary clock input (frequency) is multiplied up by the system phase-locked loop (PLL) and the clock unit to create the coherent system bus clock (*csb_clk*), the internal clock for the DDR controller (*ddr_clk*), and the internal clock for the local bus interface unit (*lbiu_clk*).

The *csb_clk* frequency is derived from a complex set of factors that can be simplified into the following equation:

$$csb\_clk = \{PCI\_SYNC\_IN \times (1 + CFG\_CLKIN\_DIV)\} \times SPMF$$

In PCI host mode, PCI_SYNC_IN × (1 + CFG_CLKIN_DIV) is the CLKIN frequency.

The *csb_clk* serves as the clock input to the e300 core. A second PLL inside the e300 core multiplies the *csb_clk* frequency to create the internal clock for the e300 core (*core_clk*). The system and core PLL multipliers are selected by the SPMF and COREPLL fields in the reset configuration word low (RCWL), which is loaded at power-on reset or by one of the hard-coded reset options. See the chapter on reset, clocking, and initialization in the *MPC8349E Reference Manual* for more information on the clock subsystem.

The internal *ddr_clk* frequency is determined by the following equation:

$$ddr\_clk = csb\_clk \times (1 + RCWL[DDRCM])$$

ddr_clk is not the external memory bus frequency; *ddr_clk* passes through the DDR clock divider (÷2) to create the differential DDR memory bus clock outputs (MCK and $\overline{\text{MCK}}$). However, the data rate is the same frequency as *ddr_clk.*

The internal *lbiu_clk* frequency is determined by the following equation:

$$lbiu\_clk = csb\_clk \times (1 + RCWL[LBIUCM])$$

lbiu_clk is not the external local bus frequency; *lbiu_clk* passes through the LBIU clock divider to create the external local bus clock outputs (LSYNC_OUT and LCLK[0:2]). The LBIU clock divider ratio is controlled by LCCR[CLKDIV].

In addition, some of the internal units may have to be shut off or operate at lower frequency than the *csb_clk* frequency. Those units have a default clock ratio that can be configured by a memory-mapped register after the device exits reset. Table 53 specifies which units have a configurable clock frequency.

Table 53. Configurable Clock Units

Unit	Default Frequency	Options
TSEC1	*csb_clk/3*	Off, *csb_clk, csb_clk/2, csb_clk/3*
TSEC2, I^2C1	*csb_clk/3*	Off, *csb_clk, csb_clk/2, csb_clk/3*
Security core	*csb_clk/3*	Off, *csb_clk,* csb_clk/2, *csb_clk/3*
USB DR, USB MPH	*csb_clk/3*	Off, csb_clk, csb_clk/2, *csb_clk/3*
PCI and DMA complex	*csb_clk*	Off, *csb_clk*

Table 58. CSB Frequency Options for Agent Mode

CFG_CLKIN_DIV at Reset[1]	SPMF	*csb_clk* : Input Clock Ratio[2]	Input Clock Frequency (MHz)[2]			
			16.67	25	33.33	66.67
			csb_clk Frequency (MHz)			
Low	0010	2 : 1				133
Low	0011	3 : 1			100	200
Low	0100	4 : 1		100	133	266
Low	0101	5 : 1		125	166	333
Low	0110	6 : 1	100	150	200	
Low	0111	7 : 1	116	175	233	
Low	1000	8 : 1	133	200	266	
Low	1001	9 : 1	150	225	300	
Low	1010	10 : 1	166	250	333	
Low	1011	11 : 1	183	275		
Low	1100	12 : 1	200	300		
Low	1101	13 : 1	216	325		
Low	1110	14 : 1	233			
Low	1111	15 : 1	250			
Low	0000	16 : 1	266			
High	0010	4 : 1		100	133	266
High	0011	6 : 1	100	150	200	
High	0100	8 : 1	133	200	266	
High	0101	10 : 1	166	250	333	
High	0110	12 : 1	200	300		
High	0111	14 : 1	233			
High	1000	16 : 1	266			

1 CFG_CLKIN_DIV doubles csb_clk if set high.

2 CLKIN is the input clock in host mode; PCI_CLK is the input clock in agent mode.
DDR2 memory may be used at 133 MHz provided that the memory components are specified for operation at this frequency.

19.2 Core PLL Configuration

RCWL[COREPLL] selects the ratio between the internal coherent system bus clock (*csb_clk*) and the e300 core clock (*core_clk*). Table 59 shows the encodings for RCWL[COREPLL]. COREPLL values that are not listed in Table 59 should be considered as reserved.

Table 60. Suggested PLL Configurations

Ref No.[1]	RCWL		400 MHz Device			533 MHz Device			667 MHz Device		
	SPMF	CORE PLL	Input Clock Freq (MHz)[2]	CSB Freq (MHz)	Core Freq (MHz)	Input Clock Freq (MHz)[2]	CSB Freq (MHz)	Core Freq (MHz)	Input Clock Freq (MHz)[2]	CSB Freq (MHz)	Core Freq (MHz)
33 MHz CLKIN/PCI_CLK Options											
922	**1001**	**0100010**	—	—	—	—	—	f300	33	300	300
723	**0111**	**0100011**	33	233	350	33	233	350	33	233	350
604	**0110**	**0000100**	33	200	400	33	200	400	33	200	400
624	**0110**	**0100100**	33	200	400	33	200	400	33	200	400
803	**1000**	**0000011**	33	266	400	33	266	400	33	266	400
823	**1000**	**0100011**	33	266	400	33	266	400	33	266	400
903	**1001**	**0000011**	—			33	300	450	33	300	450
923	**1001**	**0100011**	—			33	300	450	33	300	450
704	**0111**	**0000011**	—			33	233	466	33	233	466
724	**0111**	**0100011**	—			33	233	466	33	233	466
A03	**1010**	**0000011**	—			33	333	500	33	333	500
804	**1000**	**0000100**	—			33	266	533	33	266	533
705	**0111**	**0000101**	—			—			33	233	583
606	**0110**	**0000110**	—			—			33	200	600
904	**1001**	**0000100**	—			—			33	300	600
805	**1000**	**0000101**	—			—			33	266	667
A04	**1010**	**0000100**	—			—			33	333	667
66 MHz CLKIN/PCI_CLK Options											
304	**0011**	**0000100**	66	200	400	66	200	400	66	200	400
324	**0011**	**0100100**	66	200	400	66	200	400	66	200	400
403	**0100**	**0000011**	66	266	400	66	266	400	66	266	400
423	**0100**	**0100011**	66	266	400	66	266	400	66	266	400
305	**0011**	**0000101**	—			66	200	500	66	200	500
503	**0101**	**0000011**	—			66	333	500	66	333	500
404	**0100**	**0000100**	—			66	266	533	66	266	533
306	**0011**	**0000110**	—			—			66	200	600
405	**0100**	**0000101**	—			—			66	266	667
504	**0101**	**0000100**	—			—			66	333	667

1 The PLL configuration reference number is the hexadecimal representation of RCWL, bits 4–15 associated with the SPMF and COREPLL settings given in the table.

2 The input clock is CLKIN for PCI host mode or PCI_CLK for PCI agent mode.

where:

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

$R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)

$R_{\theta CA}$ = case-to-ambient thermal resistance (°C/W)

$R_{\theta JC}$ is device-related and cannot be influenced by the user. The user controls the thermal environment to change the case-to-ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed-circuit board, or change the thermal dissipation on the printed-circuit board surrounding the device.

The thermal performance of devices with heat sinks has been simulated with a few commercially available heat sinks. The heat sink choice is determined by the application environment (temperature, air flow, adjacent component power dissipation) and the physical space available. Because there is not a standard application environment, a standard heat sink is not required.

Table 63 and Table 64 show heat sink thermal resistance for TBGA and PBGA of the MPC8347E.

Table 63. Heat Sink and Thermal Resistance of MPC8347E (TBGA)

Heat Sink Assuming Thermal Grease	Air Flow	35 × 35 mm TBGA
		Thermal Resistance
AAVID 30 × 30 × 9.4 mm pin fin	Natural convection	10
AAVID 30 × 30 × 9.4 mm pin fin	1 m/s	6.5
AAVID 30 × 30 × 9.4 mm pin fin	2 m/s	5.6
AAVID 31 × 35 × 23 mm pin fin	Natural convection	8.4
AAVID 31 × 35 × 23 mm pin fin	1 m/s	4.7
AAVID 31 × 35 × 23 mm pin fin	2 m/s	4
Wakefield, 53 × 53 × 25 mm pin fin	Natural convection	5.7
Wakefield, 53 × 53 × 25 mm pin fin	1 m/s	3.5
Wakefield, 53 × 53 × 25 mm pin fin	2 m/s	2.7
MEI, 75 × 85 × 12 no adjacent board, extrusion	Natural convection	6.7
MEI, 75 × 85 × 12 no adjacent board, extrusion	1 m/s	4.1
MEI, 75 × 85 × 12 no adjacent board, extrusion	2 m/s	2.8
MEI, 75 × 85 × 12 mm, adjacent board, 40 mm side bypass	1 m/s	3.1

Table 64. Heat Sink and Thermal Resistance of MPC8347E (PBGA)

Heat Sink Assuming Thermal Grease	Air Flow	29 × 29 mm PBGA
		Thermal Resistance
AAVID 30 × 30 × 9.4 mm pin fin	Natural convection	13.5
AAVID 30 × 30 × 9.4 mm pin fin	1 m/s	9.6

21.3 Decoupling Recommendations

Due to large address and data buses and high operating frequencies, the MPC8347E can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the MPC8347E system, and the MPC8347E itself requires a clean, tightly regulated source of power. Therefore, the system designer should place at least one decoupling capacitor at each V_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} pin of the MPC8347E. These capacitors should receive their power from separate V_{DD}, OV_{DD}, GV_{DD}, LV_{DD}, and GND power planes in the PCB, with short traces to minimize inductance. Capacitors can be placed directly under the device using a standard escape pattern. Others can surround the part.

These capacitors should have a value of 0.01 or 0.1 µF. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, distribute several bulk storage capacitors around the PCB, feeding the V_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors are 100–330 µF (AVX TPS tantalum or Sanyo OSCON).

21.4 Connection Recommendations

To ensure reliable operation, connect unused inputs to an appropriate signal level. Unused active low inputs should be tied to OV_{DD}, GV_{DD}, or LV_{DD} as required. Unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected.

Power and ground connections must be made to all external V_{DD}, GV_{DD}, LV_{DD}, OV_{DD}, and GND pins of the MPC8347E.

21.5 Output Buffer DC Impedance

The MPC8347E drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see Figure 43). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

Table 68. SVR Settings (continued)

MPC8347E	PBGA	8054_0010
MPC8347	PBGA	8055_0010

23.2 Part Marking

Parts are marked as in the example shown in Figure 44.

Notes:
ATWLYYWW is the traceability code.
CCCCC is the country code.
MMMMM is the mask number.
YWWLAZ is the assembly traceability code.

Figure 44. Freescale Part Marking for TBGA or PBGA Devices